



## STS5N15F4

N-channel 150 V, 0.057Ω, 5 A, SO-8  
STripFET™ DeepGATE™ Power MOSFET

### Features

Type	V <sub>DSS</sub>	R <sub>DS(on) max</sub>	I <sub>D</sub>
STS5N15F4	150 V	< 0.063 Ω	5 A

- N-channel enhancement mode
- 100% avalanche rated
- Low gate charge
- Very low on-resistance

### Application

- Switching applications

### Description

This STripFET™ DeepGATE™ Power MOSFET technology is among the latest improvements, which have been especially tailored to minimize on-state resistance, with a new gate structure, providing superior switching performances.

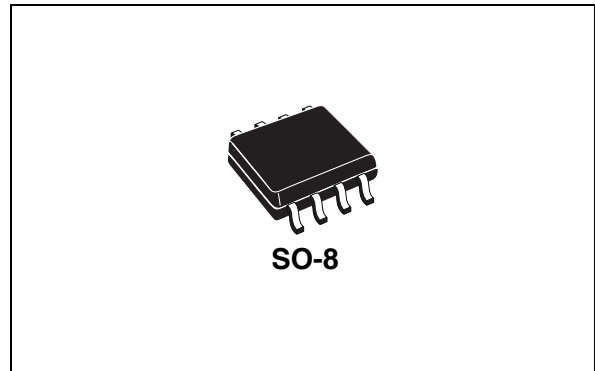


Figure 1. Internal schematic diagram

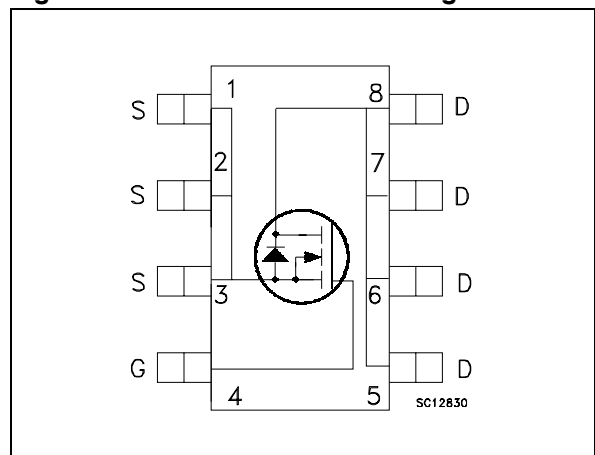


Table 1. Device summary

Order code	Marking	Package	Packaging
STS5N15F4	5U15-	SO-8	Tape and reel

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	150	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	5	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	3	A
$I_{DM}^{(1)}$	Drain current (pulsed)	20	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	2.5	W
$T_{stg}$	Storage temperature	-55 to 150	$^\circ\text{C}$
$T_j$	Operating junction temperature		

1. Pulse width limited by safe operating area

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	50	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1 inch<sup>2</sup>, 2 oz Cu,  $t < 10$  sec

**Table 4. Avalanche characteristics**

Symbol	Parameter	Max value	Unit
$I_{AS}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	5	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AS}$ , $V_{DD} = 140\text{ V}$ )	125	mJ

## 2 Electrical characteristics

( $T_J = 25\text{ °C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	150			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 150\text{ V}$ , $V_{DS} = 150\text{ V}$ , @ $125\text{ °C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 2.5\text{ A}$		0.057	0.063	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	2710	-	pF
$C_{oss}$	Output capacitance			180		pF
$C_{rss}$	Reverse transfer capacitance			69.5		pF
$Q_g$	Total gate charge	$V_{DD} = 75\text{ V}$ , $I_D = 5\text{ A}$ $V_{GS} = 10\text{ V}$ <i>Figure 14 on page 7</i>	-	48	-	nC
$Q_{gs}$	Gate-source charge			10.8		nC
$Q_{gd}$	Gate-drain charge			13.7		nC
$R_g$	Gate input resistance	$f = 1\text{ MHz}$ Gate DC Bias = 0 Test signal level = 20 mV open drain	-	1.9	-	$\Omega$

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=75\text{ V}$ , $I_D=3\text{ A}$ , $R_G=4.7\ \Omega$ , $V_{GS}=10\text{ V}$ <i>Figure 13 on page 7</i>	-	13.5	-	ns
$t_r$	Rise time			5.1		ns
$t_{d(off)}$	Turn-off delay time			39.7		ns
$t_f$	Fall time			11.4		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$I_{SD}$	Source-drain current		-		5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		20	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=6\text{ A}$ , $V_{GS}=0$	-		1.3	V
$t_{rr}$	Reverse recovery time	$I_{SD}=6\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$ , $V_R=120\text{ V}$ , $T_J=150\text{ }^\circ\text{C}$ <i>Figure 15 on page 7</i>	-	85.2		ns
$Q_{rr}$	Reverse recovery charge			277.6		nC
$I_{RRM}$	Reverse recovery current			8.2		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

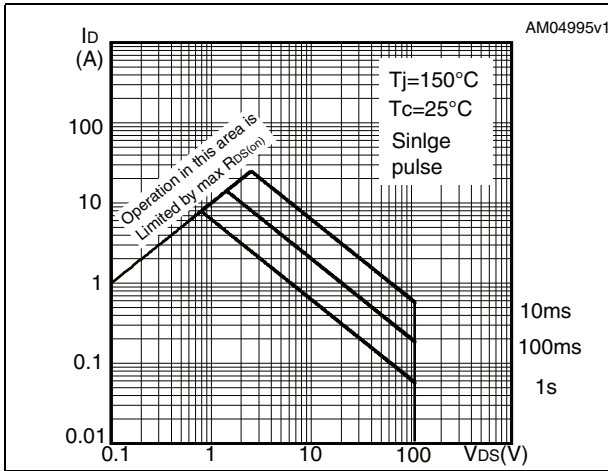


Figure 3. Thermal impedance

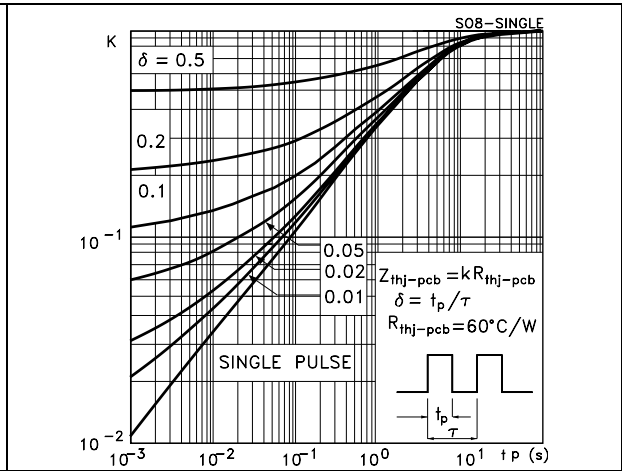


Figure 4. Output characteristics

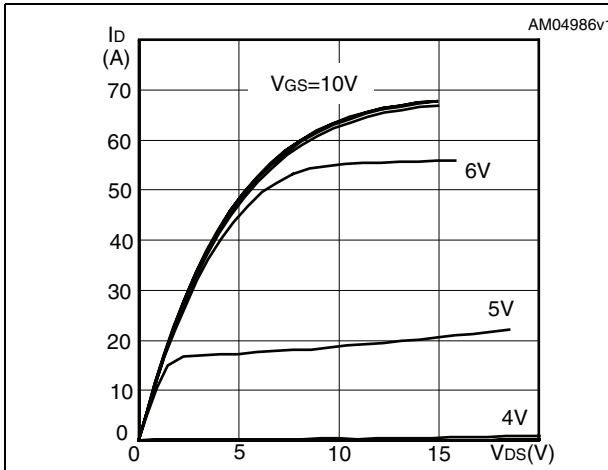


Figure 5. Transfer characteristics

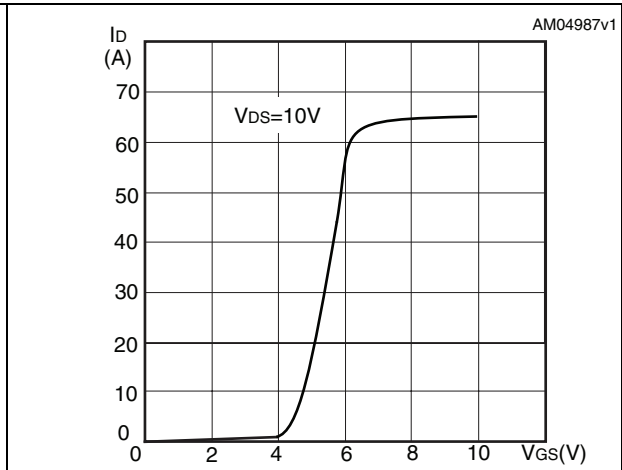


Figure 6. Normalized  $B_{V_{DS}}$  vs temperature

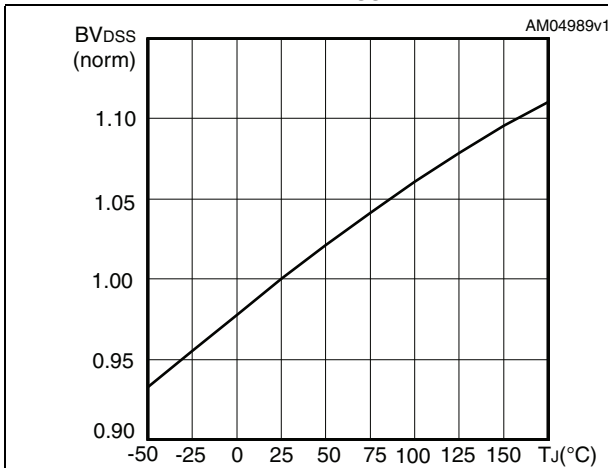
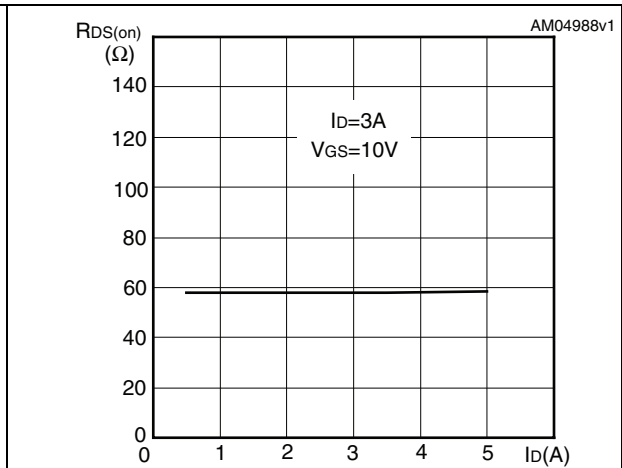
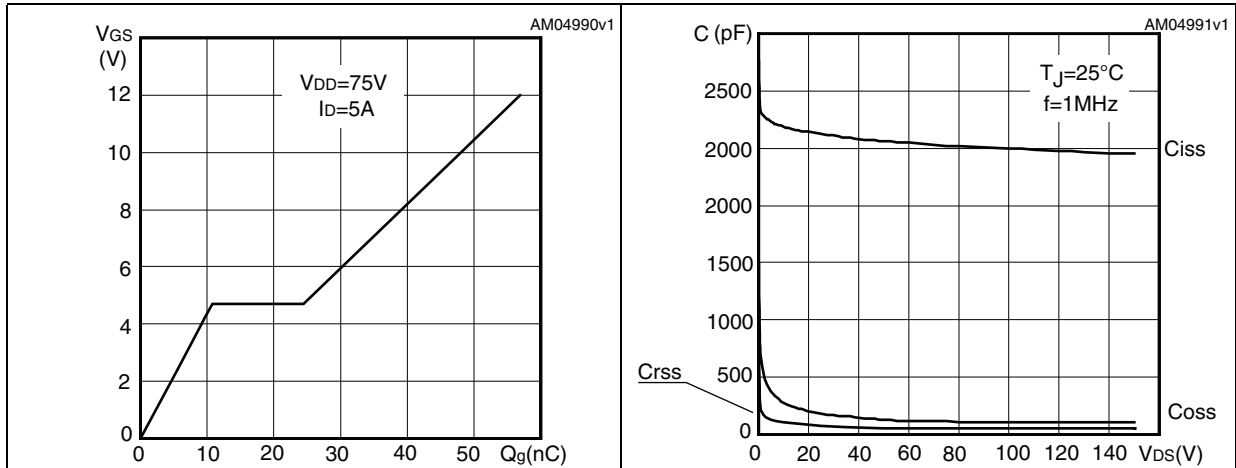


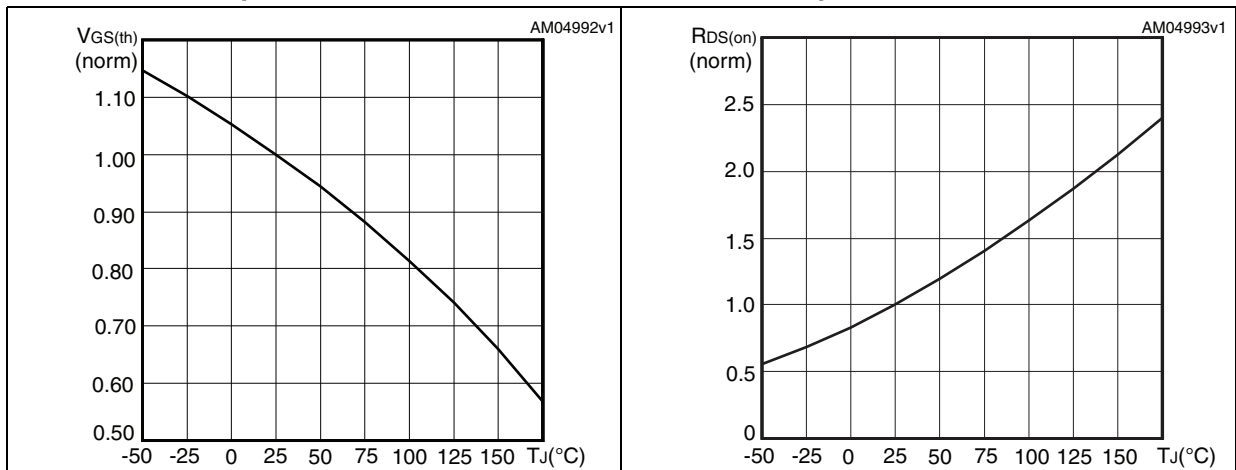
Figure 7. Static drain-source on resistance



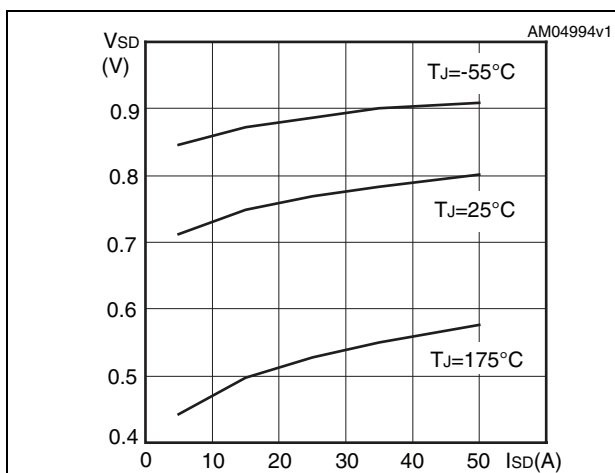
**Figure 8. Gate charge vs gate-source voltage** **Figure 9. Capacitance variations**



**Figure 10. Normalized gate threshold voltage vs temperature** **Figure 11. Normalized on resistance vs temperature**

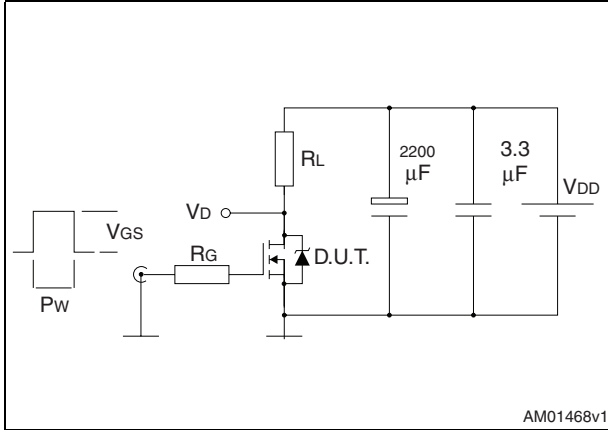


**Figure 12. Source-drain diode forward characteristics**



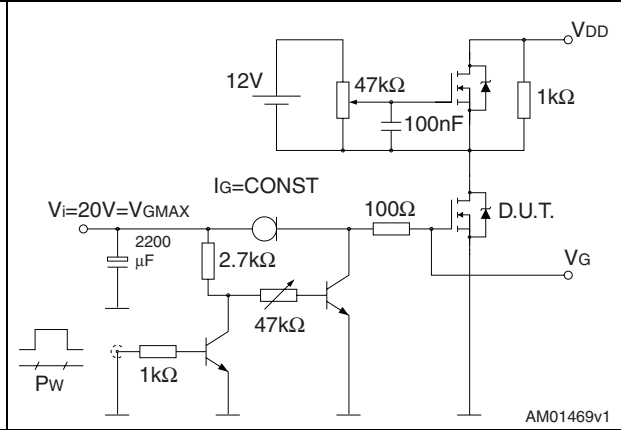
### 3 Test circuits

**Figure 13. Switching times test circuit for resistive load**



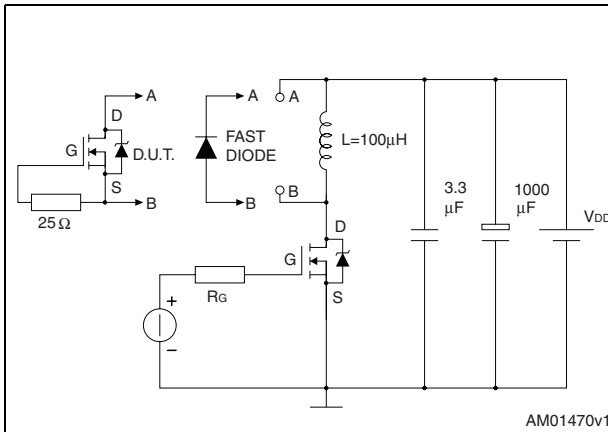
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**Figure 14. Gate charge test circuit**



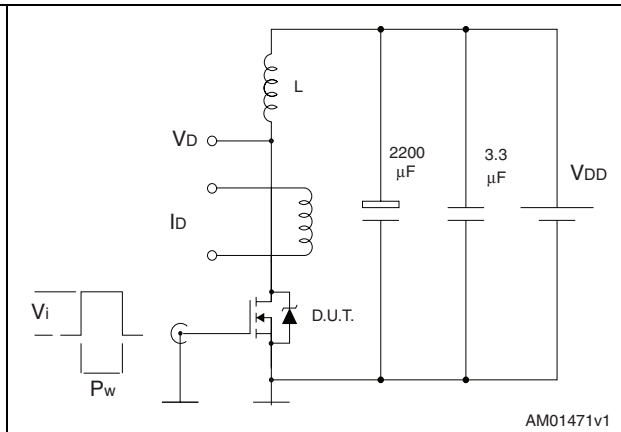
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**Figure 15. Test circuit for inductive load switching and diode recovery times**



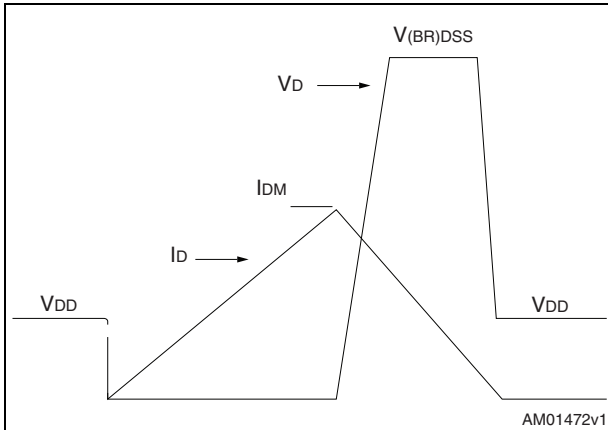
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**Figure 16. Unclamped inductive load test circuit**



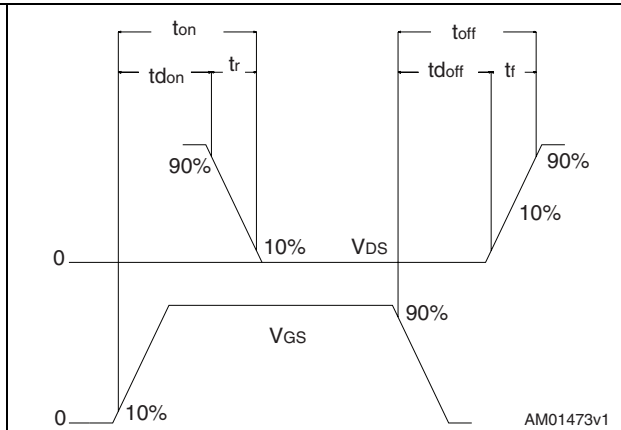
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**Figure 17. Unclamped inductive waveform**



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**Figure 18. Switching time waveform**



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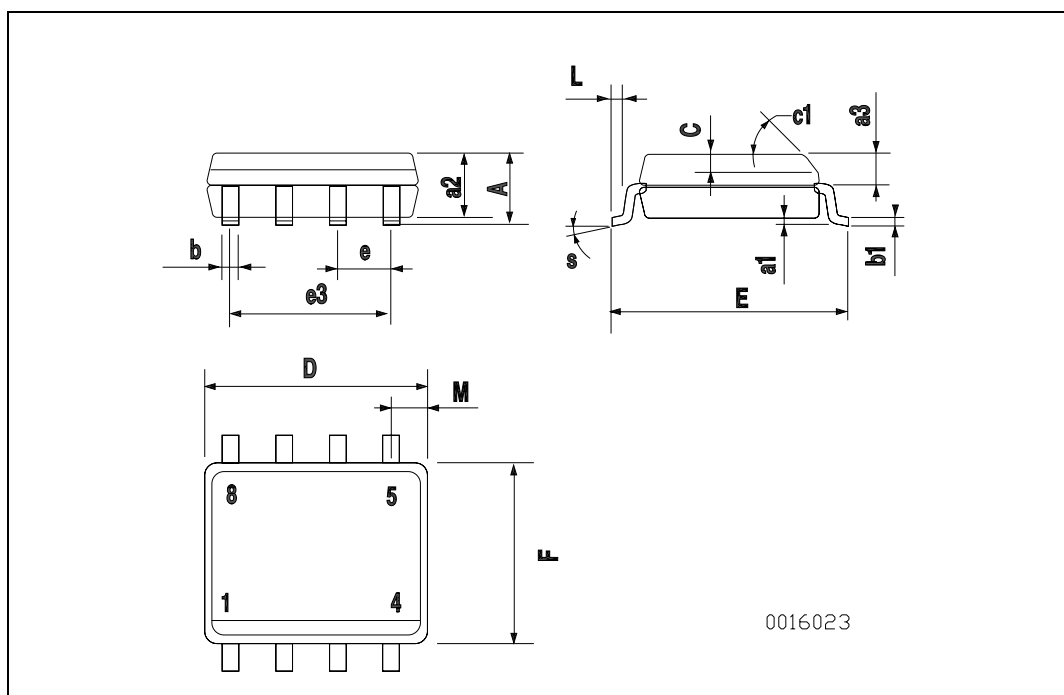
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.



## SO-8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



## 5 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
23-Jul-2009	1	First release

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